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Triacs

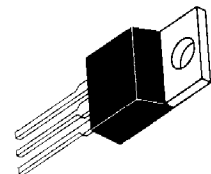
Silicon Bidirectional Triode Thyristors

... designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- Gate Triggering Guaranteed in Three Modes (MAC229 Series) or Four Modes (MAC229A Series)

MAC229 Series MAC229A Series

TRIACs
8 AMPERES RMS
200 thru 800 VOLTS



(TO-220AB)

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ ($T_J = -40$ to 110°C 1/2 Sine wave 50 to 60 Hz, Gate Open) MAC229-4, MAC229A4 MAC229-6, MAC229A6 MAC229-8, MAC229A8 MAC229-10, MAC229A10	V_{DRM}	200 400 600 800	Volts
On-State RMS Current ($T_C = 80^\circ\text{C}$) Full Cycle Sine Wave 50 to 60 Hz	$I_T(\text{RMS})$	8	Amps
Peak Non-repetitive Surge Current (One Full Cycle 60 Hz, $T_J = 110^\circ\text{C}$)	I_{TSM}	80	Amps
Circuit Fusing ($t = 8.3$ ms)	I^2t	26	A^2s
Peak Gate Current ($t \leq 2$ μs)	I_{GM}	± 2	Amps
Peak Gate Voltage ($t \leq 2$ μs)	V_{GM}	± 10	Volts
Peak Gate Power ($t \leq 2$ μs)	P_{GM}	20	Watts
Average Gate Power ($T_C = 80^\circ\text{C}$, $t \leq 8.3$ ms)	$P_{G(AV)}$	0.5	Watts
Operating Junction Temperature Range	T_J	-40 to 110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to 150	$^\circ\text{C}$
Mounting Torque		8	in. lb.

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded. (cont.)



MAC229 Series MAC229A Series

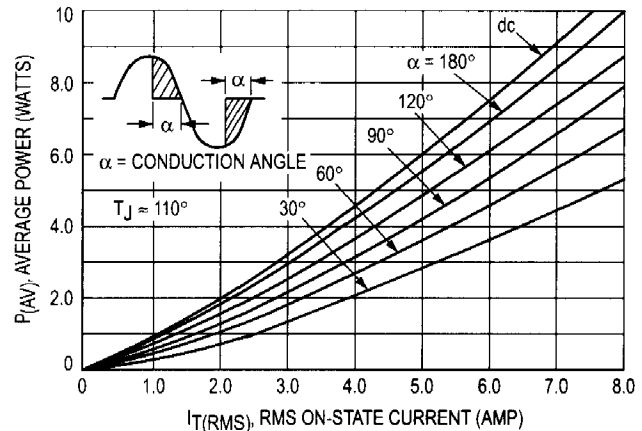
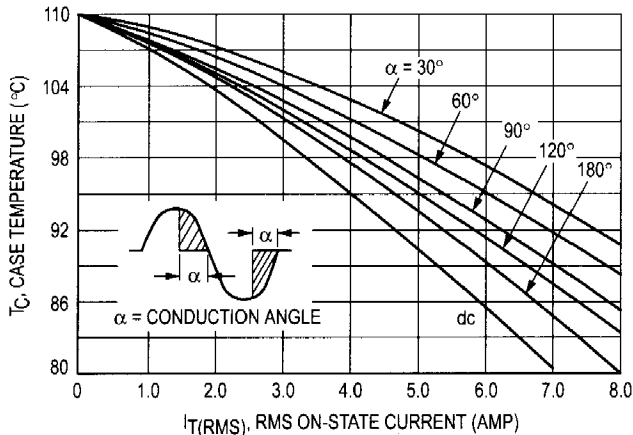
THERMAL CHARACTERISTICS

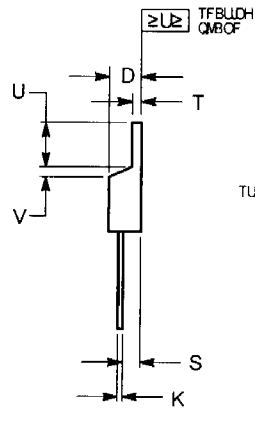
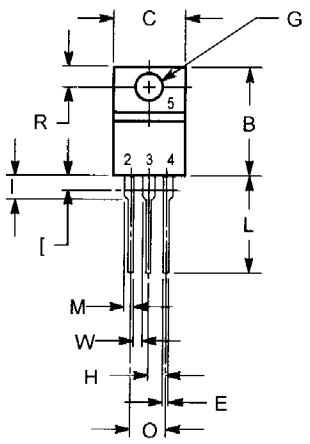
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	$^{\circ}C/W$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current ⁽¹⁾ ($V_D = \text{Rated } V_{DRM}$, Gate Open) $T_J = 25^{\circ}C$ $T_J = 110^{\circ}C$	I_{DRM}	—	—	10 2	μA mA
Peak On-State Voltage ($I_{TM} = 11 A$ Peak, Pulse Width ≤ 2 ms, Duty Cycle $\leq 2\%$)	V_{TM}	—	—	1.8	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 V$, $R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	I_{GT}	—	—	10 15	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 V$, $R_L = 100 \Omega$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY ($V_D = \text{Rated } V_{DRM}$, $T_C = 110^{\circ}C$, $R_L = 10 k$) MT2(+), G(+); MT2(+), G(-); MT2(-), G(-); MT2(-), G(+) "A" SUFFIX ONLY	V_{GT}	— —	— —	2 2.5	Volts
Holding Current ($V_D = 12 V_{dc}$, $I_{TM} = 200$ mA, Gate Open)	I_H	—	—	15	mA
Gate-Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 16 A$ Peak, $I_G = 30$ mA)	t_{gt}	—	1.5	—	μs
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Waveform, $T_C = 110^{\circ}C$)	dv/dt	—	25	—	$V/\mu s$
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11.3 A$, Commutating $di/dt = 4.1 A/ms$, Gate Unenergized, $T_C = 80^{\circ}C$)	$dv/dt(c)$	—	5	—	$V/\mu s$

1. Ratings apply for open gate conditions. Devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.





TLZMF15;
 Q.01/2/ NB.D\UFSN,DBM2
 3/ NB.D\UFSN,DBM3
 4/ HBLF
 5/ NB.D\UFSN,DBM3

OPUFT:
 2/ E.NFOT.P.O.DHBOE\UPMFSBOD.DH\OFSIBOTJ
 Z256N-12 93/
 3/ DP\USPMMADHIE.NFOT.P.O\LODI /
 4/ E.NFOT.P.O\IEFG\OFT\BI\ POFIX I FFS\BMM
 CPEZ\BOE\MBE\SSFH\MSJ\FT\BSF
 BMPXFE/

E.N	JDI FT		N.MN\FUFS T	
	N.LD	NBY	N.LD	NBY
B	1/681	1/731	25/59	26/86
C	1/491	1/516	.777	21/39
D	1/271	1/2: 1	5/18	5/93
E	1/136	1/146	1/75	1/99
G	1/253	1/258	4/72	4/84
H	1/1: 6	1/216	3/53	3/77
I	1/221	1/266	3/91	4/ 4
K	1/125	1/133	1/47	1/66
L	1/611	1/673	23/81	25/38
M	1/156	1/166	2/26	2/4
O	1/2: 1	1/321	5/94	6/44
R	1/211	1/231	3/65	4/15
S	1/191	1/221	3/15	3/8
T	1/156	1/166	2/26	2/4
U	1/346	1/366	6/ 8	7/58
V	1/111	1/161	1/11	2/38
W	1/156	>>>	2/26	>>>
[>>>	1/191	>>>	3/15